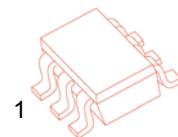


General purpose transistors (dual transistors)

FEATURES

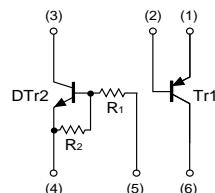
- 2SA2018 and DTC144E are housed independently in a package.
- Mounting possible with SOT-363 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area be cut in half.

SOT-363



Marking: F5

Equivalent circuit



Tr1 Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-15	V
V_{CEO}	Collector-Emitter Voltage	-12	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_c	Collector Current	-500	mA
P_c	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-15\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-10\text{mA}$	270		680	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-200\text{mA}, I_B=-10\text{mA}$			-0.25	V
Transition frequency	f_T	$V_{CE}=-2\text{V}, I_E=-10\text{mA}, f=100\text{MHz}$		260		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		6.5		pF

Tr2 Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	50	V
Input voltage	V _{IN}	-10~+40	V
Output current	I _O	30	mA
	I _{C(MAX)}	100	
Power dissipation	P _d	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~150	°C

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	V _{I(off)}			0.5	V	V _{CC} =5V, I _O =100μA
	V _{I(on)}	3.0				V _O =0.3V, I _O =2mA
Output voltage	V _{O(on)}		0.1	0.3	V	I _O /I _i =10mA/0.5mA
Input current	I _i			0.18	mA	V _i =5V
Output current	I _{O(off)}			0.5	μA	V _{CC} =50V, V _i =0
DC current gain	G _i	68				V _O =5V, I _O =5mA
Input resistance	R _i	32.9	47	61.1	KΩ	-
Resistance ratio	R ₂ /R ₁	0.8	1	1.2		-
Transition frequency	f _T		250		MHz	V _{CE} =10V, I _E =-5mA, f=100MHz